

Description

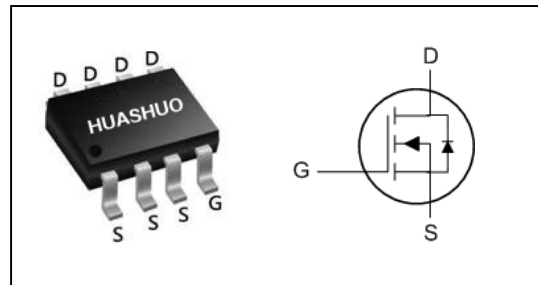
The HSM3014 is the high cell density trenched N-ch MOSFETs, which provide excellent $R_{DS(ON)}$ and gate charge for most of the synchronous buck converter applications.

The HSM3014 meet the RoHS and Green Product requirement 100% EAS guaranteed with full function reliability approved.

- 100% EAS Guaranteed
- Green Device Available
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology

Product Summary

V_{DS}	30	V
$R_{DS(ON),max}$	12	m Ω
I_D	9	A

SOP8 Pin Configuration

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_A=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	9	A
$I_D@T_A=70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	7	A
I_{DM}	Pulsed Drain Current ²	36	A
EAS	Single Pulse Avalanche Energy ³	24.2	mJ
I_{AS}	Avalanche Current	22	A
$P_D@T_A=25^\circ C$	Total Power Dissipation ⁴	1.5	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	85	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	25	$^\circ C/W$

Electrical Characteristics ($T_J=25\text{ }^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	30	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=1\text{mA}$	---	0.023	---	$V/^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V, I_D=8A$	---	10	12	m Ω
		$V_{GS}=4.5V, I_D=6A$	---	15	18	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2	1.5	2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-5.08	---	$\text{mV}/^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=24V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=24V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=5V, I_D=8A$	---	24	---	S
R_g	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1\text{MHz}$	---	1.8	3	Ω
Q_g	Total Gate Charge (4.5V)	$V_{DS}=15V, V_{GS}=4.5V, I_D=8A$	---	9.63	13.5	nC
Q_{gs}	Gate-Source Charge		---	3.88	5.4	
Q_{gd}	Gate-Drain Charge		---	3.44	4.8	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=15V, V_{GS}=10V, R_G=1.5\Omega, I_D=8A$	---	4.2	8.4	ns
T_r	Rise Time		---	8.2	15	
$T_{d(off)}$	Turn-Off Delay Time		---	31	62	
T_f	Fall Time		---	4	8	
C_{iss}	Input Capacitance	$V_{DS}=15V, V_{GS}=0V, f=1\text{MHz}$	---	940	1316	pF
C_{oss}	Output Capacitance		---	131	183	
C_{rss}	Reverse Transfer Capacitance		---	109	153	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,5}	$V_G=V_D=0V$, Force Current	---	---	9	A
I_{SM}	Pulsed Source Current ^{2,5}		---	---	36	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=1A, T_J=25^\circ\text{C}$	---	---	1	V
t_{rr}	Reverse Recovery Time	$I_F=8A, dI/dt=100A/\mu s, T_J=25^\circ\text{C}$	---	8	---	nS
Q_{rr}	Reverse Recovery Charge		---	2.9	---	nC

Note :

- 1.The data tested by surface mounted on a 1 inch²FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD}=25V, V_{GS}=10V, L=0.1\text{mH}, I_{AS}=22A$
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.



N-Ch 30V Fast Switching MOSFETs

Typical Characteristics

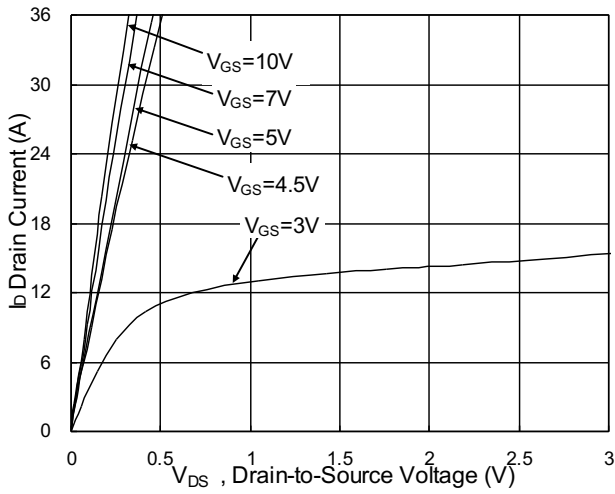


Fig.1 Typical Output Characteristics

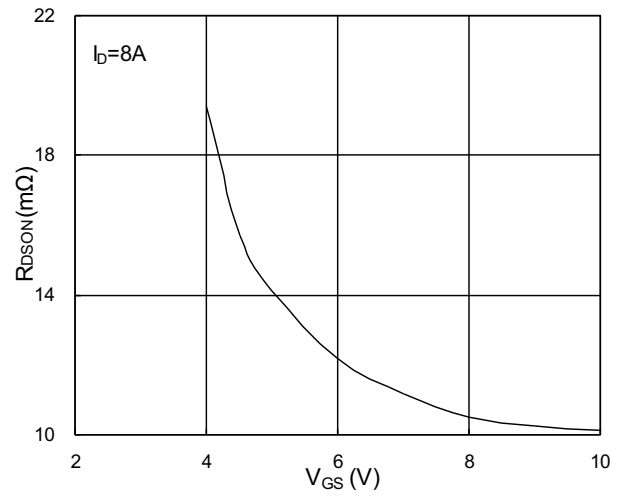


Fig.2 On-Resistance vs. G-S Voltage

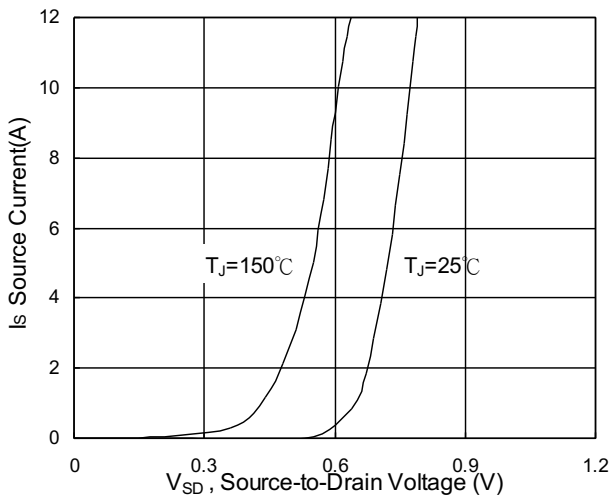


Fig.3 Forward Characteristics of Reverse

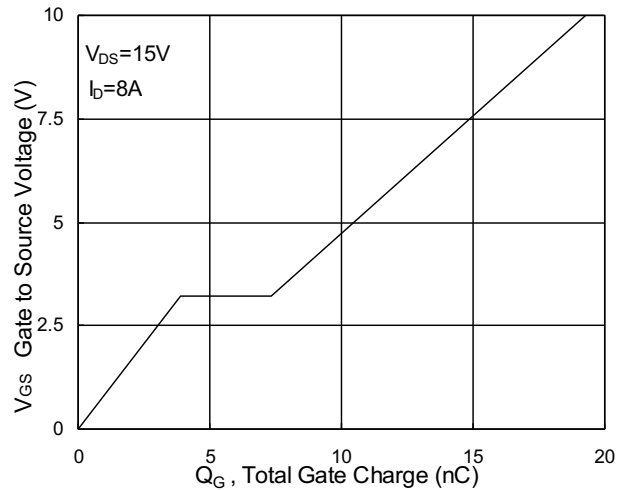


Fig.4 Gate-Charge Characteristics

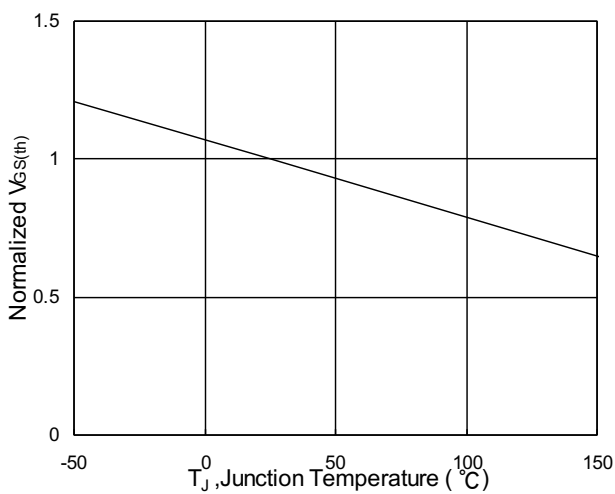


Fig.5 Normalized V_{GS(th)} vs. T_J

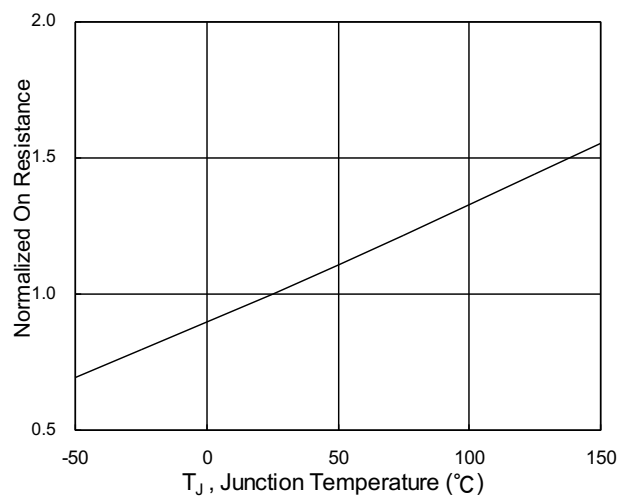


Fig.6 Normalized R_{DS(on)} vs. T_J



N-Ch 30V Fast Switching MOSFETs

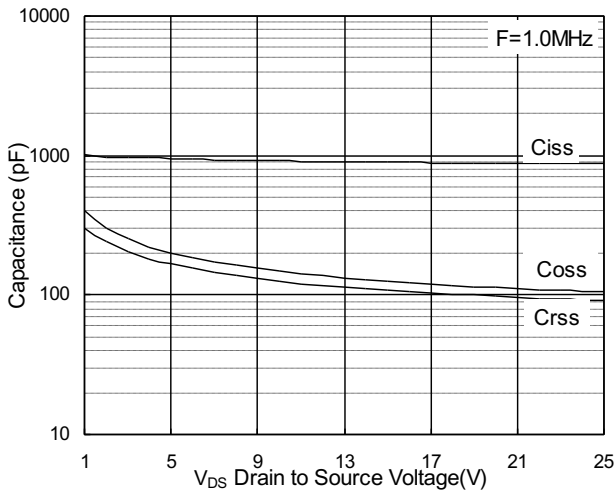


Fig.7 Capacitance

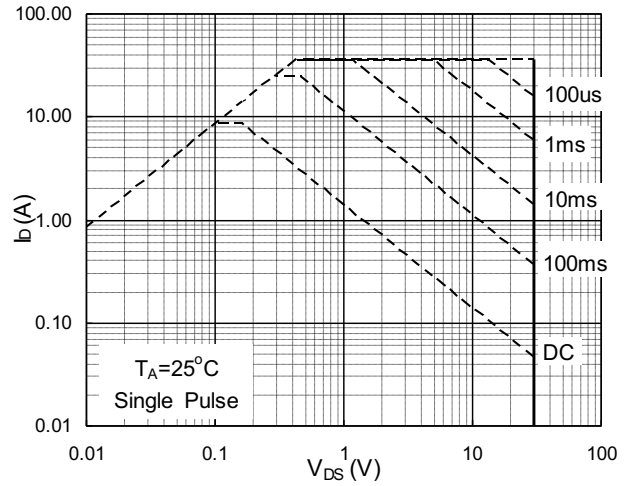


Fig.8 Safe Operating Area

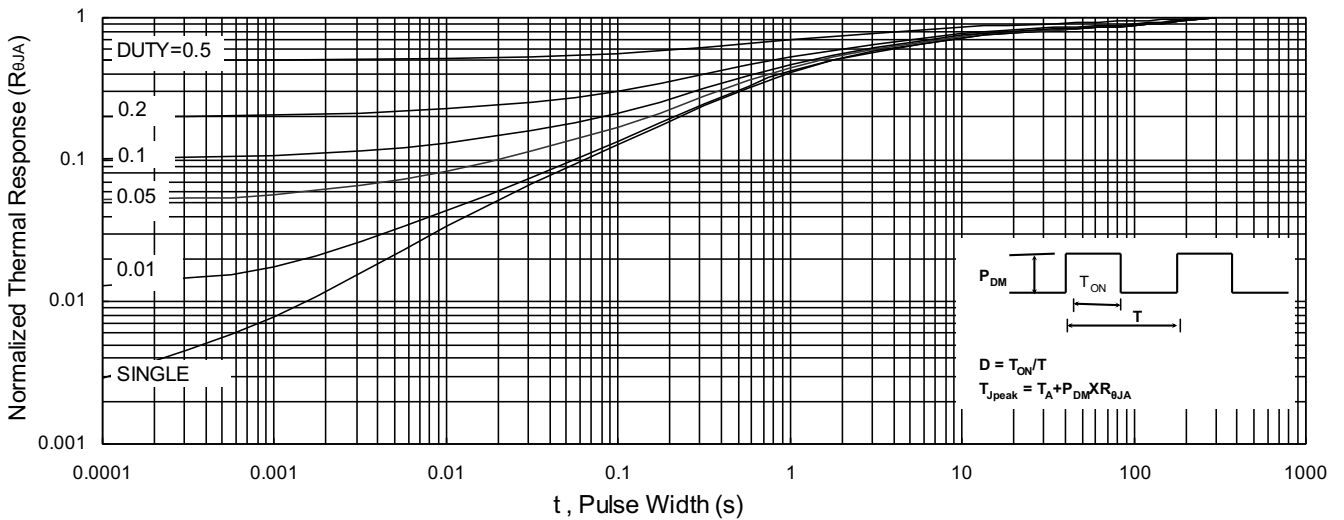


Fig.9 Normalized Maximum Transient Thermal Impedance

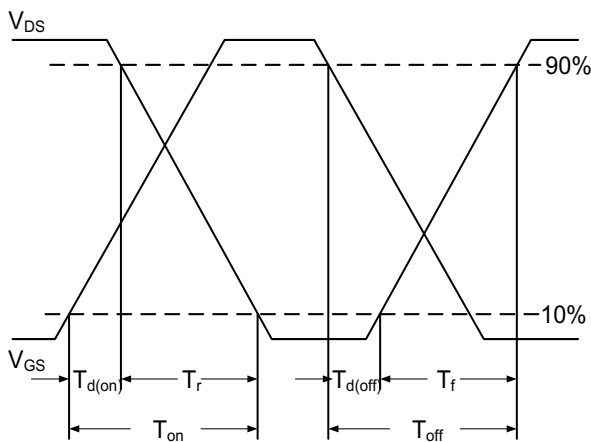


Fig.10 Switching Time Waveform

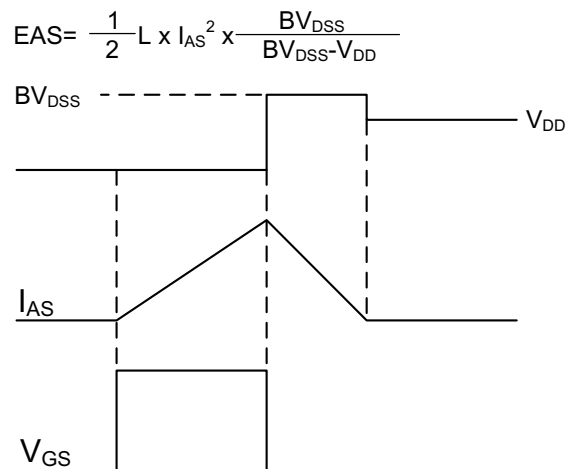


Fig.11 Unclamped Inductive Switching Waveform

Ordering Information

Part Number	Package code	Packaging
HSM3014	SOP-8	2500/Tape&Reel

